

## High voltage fast-switching NPN power transistor

**Datasheet - production data** 

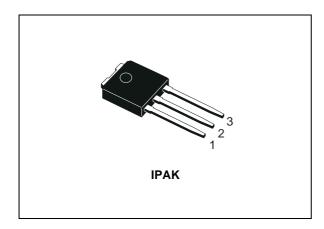
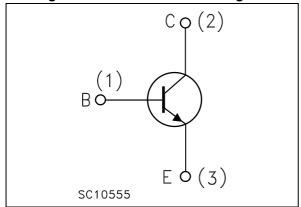


Figure 1. Internal schematic diagram



#### **Features**

- · High voltage capability
- Low spread of dynamic parameters
- · Very high switching speed

#### **Application**

Switch mode power supplies (AC-DC converters)

#### **Description**

This device is manufactured using high voltage multi epitaxial planar technology for high switching speeds and high voltage capability. It uses a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining a wide RBSOA.

**Table 1. Device summary** 

Order code	Marking	Package	Packaging
STU13005N	U13005N	IPAK	Tube

Contents STU13005N

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STU13005N Electrical ratings

# 1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V <sub>CES</sub>	Collector-emitter voltage (V <sub>BE</sub> = 0)	700	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	400	V
V <sub>EBO</sub>	Emitter-base voltage ( $I_C = 0$ ; $I_B = 1.5 \text{ A}$ ; $t_p < 10 \text{ ms}$ )	V <sub>(BR)EBO</sub>	V
I <sub>C</sub>	Collector current	3	А
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	6	А
I <sub>B</sub>	Base current	1.5	А
I <sub>BM</sub>	Base peak current (t <sub>P</sub> < 5 ms)	3	А
P <sub>TOT</sub>	Total dissipation at T <sub>c</sub> = 25 °C	30	W
T <sub>STG</sub>	Storage temperature	-65 to 150	°C
T <sub>J</sub>	Max. operating junction temperature	150	°C

Table 3. Thermal data

	Symbol	Parameter	Value	Unit
ĺ	$R_{thJC}$	Thermal resistance junction-case max	4.2	°C/W

Electrical characteristics STU13005N

## 2 Electrical characteristics

 $T_{case}$  = 25 °C unless otherwise specified.

**Table 4. Electrical characteristics** 

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector cut-off current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 700 V V <sub>CE</sub> = 700 V T <sub>C</sub> = 125 °C			1 5	mA mA
I <sub>CEO</sub>	Collector-cut-off current (I <sub>B</sub> = 0)	V <sub>CE</sub> = 400 V			1	mA
V <sub>(BR)EBO</sub>	Emitter base breakdown voltage (I <sub>C</sub> = 0)	e I <sub>E</sub> = 10 mA			18	<b>V</b>
V <sub>CEO(sus)</sub> (1)	Collector-emitter sustaining voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 10 mA	400			>
V <sub>CE(sat)</sub> (1)	Collector-emitter saturation voltage	$\begin{split} I_{C} &= 1 \text{A} & I_{B} = 200 \text{ mA} \\ I_{C} &= 2 \text{A} & I_{B} = 500 \text{ mA} \\ I_{C} &= 3 \text{A} & I_{B} = 750 \text{ mA} \end{split}$			0.5 0.6 5	> >
V <sub>BE(sat)</sub> (1)	Base-emitter saturation voltage	$I_C = 1A$ $I_B = 200 \text{ mA}$ $I_C = 2A$ $I_B = 500 \text{ mA}$			1.2 1.6	> >
h <sub>FE</sub> <sup>(1)</sup>	DC current gain	$\begin{split} I_{C} &= 500 \; \mu A & V_{CE} &= 2 \; V \\ I_{C} &= 425 \; mA & V_{CE} &= 2 \; V \\ I_{C} &= 1 \; A & V_{CE} &= 5 \; V \\ I_{C} &= 2 \; A & V_{CE} &= 5 \; V \end{split}$	15 24 10 8		30 24	
t <sub>s</sub>	Resistive load Storage time Fall time	$I_C = 2 \text{ A}$ $V_{CC} = 125 \text{ V}$ $I_{B1} = -I_{B2} = 400 \text{ mA}$ $t_p = 30  \mu\text{s}$		1.65 260		μs ns
t <sub>s</sub>	Inductive load Storage time Fall time			0.8 150		μs ns

<sup>1.</sup> Pulse test: pulse duration  $\leq$  300 µs, duty cycle  $\leq$  2 %



#### 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

10<sup>1</sup>

PULSE OPERATION \*

10<sup>8</sup>

10 | Lc MAX | PULSE OPERATION \*

10 | Lc MAX | PULSE OPERATION \*

10 | Lc MAX | PULSE OPERATION | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 1

Figure 3. Derating curve

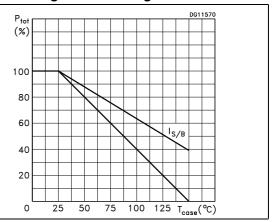


Figure 4. Reverse biased SOA

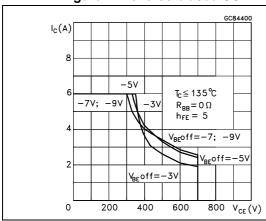


Figure 5. Output characteristics

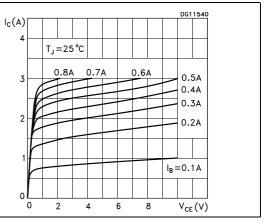


Figure 6. DC current gain  $(V_{CE} = 1 V)$ 

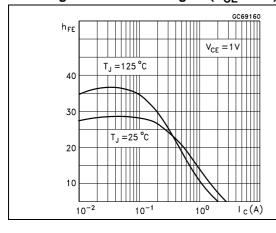
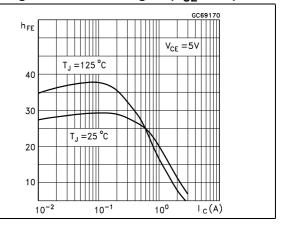


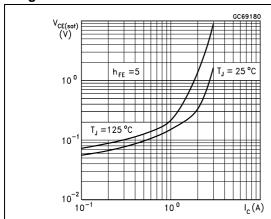
Figure 7. DC current gain  $(V_{CE} = 5 V)$ 



Electrical characteristics STU13005N

Figure 8. Collector-emitter saturation voltage

Figure 9. Base-emitter saturation voltage



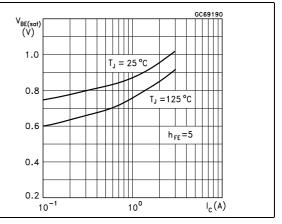
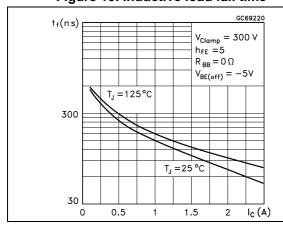


Figure 10. Inductive load fall time

Figure 11. Inductive load storage time



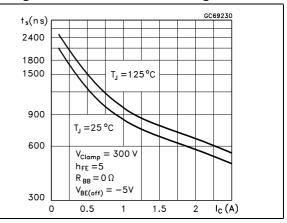
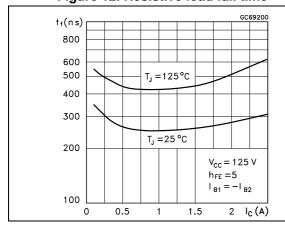
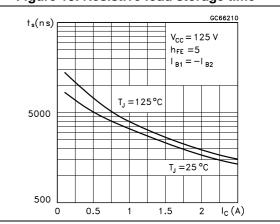


Figure 12. Resistive load fall time

Figure 13. Resistive load storage time





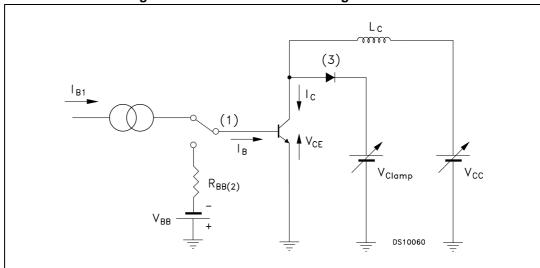
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STU13005N Test circuits

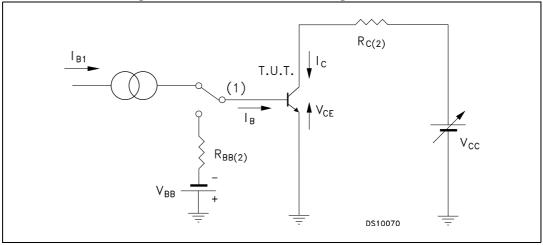
## 3 Test circuits

Figure 14. Inductive load switching test circuit



- 1) Fast electronic switch
- 2) Non-inductive resistor
- 3) Fast recovery rectifier

Figure 15. Resistive load switching test circuit



- 1) Fast electronic switch
- 2) Non-inductive resistor

## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

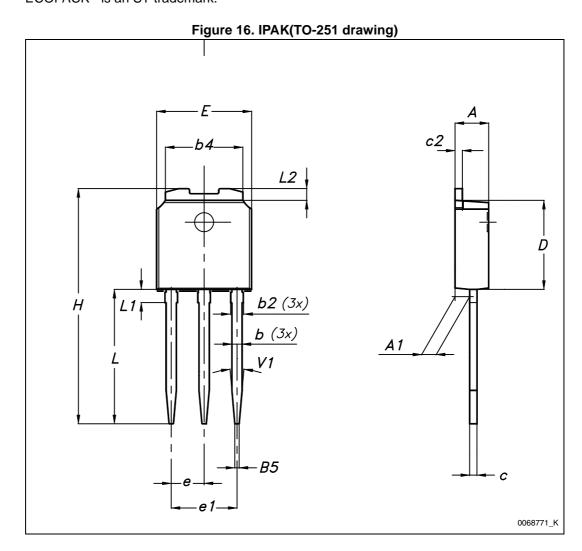


Table 5. IPAK (TO-251) mechanical data

DIM		mm.	
DIM	min.	typ.	max.
А	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
С	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
е		2.28	
e1	4.40		4.60
Н		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	



Revision history STU13005N

# 5 Revision history

**Table 6. Document revision history** 

Date	Revision	Changes
20-Feb-2012	1	First release.
09-May-2014	2	Updated Table 1: Device summary and updated Figure 4: Package mechanical data

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